## 1. General description

Dual Standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC-Q101 standard for use in high performance automotive applications.

#### 2. Features and benefits

- Dual MOSFET
- AEC-Q101 compliant
- · Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V<sub>GS(th)</sub> rating of greater than 1 V at 175 °C

## 3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Limiting values	Limiting values FET1 and FET2						
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	80	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	23	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	68	W
Static characte	eristics FET1 and FET2					•	
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 25 °C; Fig. 11		-	11.2	15	mΩ
Dynamic chara	acteristics FET1 and FE	T2			•	•	
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	11.3	-	nC
Source-drain d	Source-drain diode FET1 and FET2						
Q <sub>r</sub>	recovered charge	$I_S$ = 10 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 25 V; $T_j$ = 25 °C		-	37.7	-	nC



### Dual N-channel 80 V, 15 m $\Omega$ standard level MOSFET

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4	
8	D1	drain1	LFPAK56D (SOT1205)	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
BUK7K15-80E	LFPAK56D	plastic, single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

# 7. Marking

## **Table 4. Marking codes**

Type number	Marking code
BUK7K15-80E	71580E

#### Dual N-channel 80 V, 15 mΩ standard level MOSFET

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Limiting val	ues FET1 and FET2		'	'	_	
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	80	V
$V_{DGR}$	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	80	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		20	-20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	68	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	23	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	16	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	92	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode FET1 and FET2			•		
Is	source current	T <sub>mb</sub> = 25 °C		-	23	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	92	Α
Avalanche r	ruggedness FET1 and FET2					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 23 A; $V_{sup} \le 80$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[1] [2]	-	133	mJ

- Single-pulse avalanche rating limited by maximum junction temperature of 175  $^{\circ}\text{C}.$  Refer to application note AN10273 for further information.

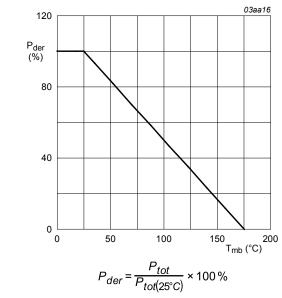


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

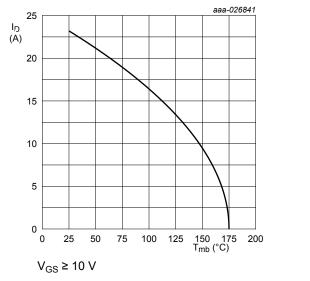
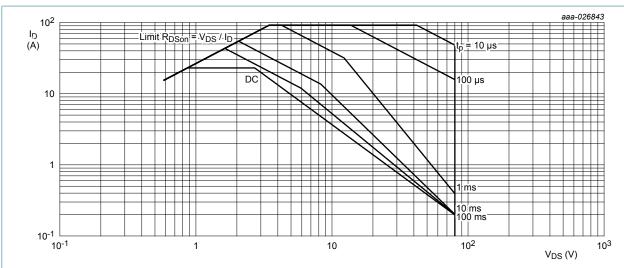


Fig. 2. Continuous drain current as a function of mounting base temperature, FET1 and FET2

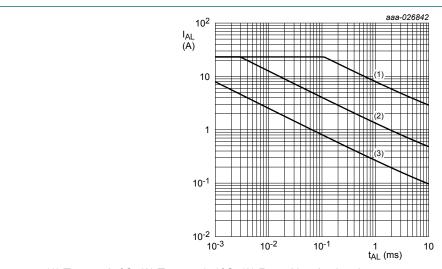
BUK7K15-80E

### Dual N-channel 80 V, 15 m $\Omega$ standard level MOSFET



 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage, FET1 and FET2



(1)  $T_{j \text{ (init)}}$  = 25°C; (2)  $T_{j \text{ (init)}}$  = 150°C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

### Dual N-channel 80 V, 15 m $\Omega$ standard level MOSFET

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	2.21	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

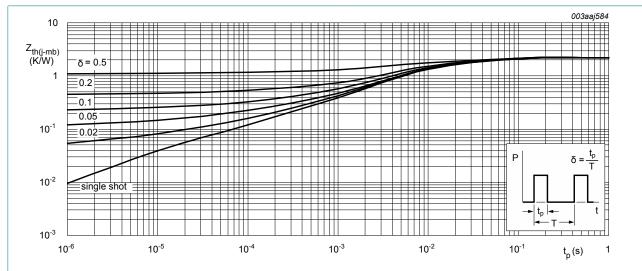


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration, FET1 and FET2

## Dual N-channel 80 V, 15 m $\Omega$ standard level MOSFET

## 10. Characteristics

#### Table 7. Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
teristics FET1 and FET2				'	
drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	80	-	-	V
breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	72	-	-	V
gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	2.4	3	4	V
	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 10	-	-	4.5	V
	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; Fig. 10	1	-	-	V
drain leakage current	V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.03	1	μΑ
	V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 10 A; $T_{j}$ = 25 °C; Fig. 11	-	11.2	15	mΩ
	$V_{GS}$ = 10 V; $I_{D}$ = 10 A; $T_{j}$ = 175 °C; Fig. 12	-	-	38	mΩ
racteristics FET1 and FE	T2			'	
total gate charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 64 V; V <sub>GS</sub> = 10 V;	-	35.1	-	nC
gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	7.4	-	nC
gate-drain charge		-	11.3	-	nC
input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	1847	2457	pF
output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	194	233	pF
reverse transfer capacitance		-	115	158	pF
turn-on delay time	$V_{DS} = 60 \text{ V}; R_L = 5 \Omega; V_{GS} = 10 \text{ V};$	-	8.8	-	ns
rise time	$R_{G(ext)} = 5 \Omega$ ; $T_j = 25 °C$	-	12.6	-	ns
turn-off delay time		-	25.1	-	ns
fall time		-	15.1	-	ns
diode FET1 and FET2				'	
source-drain voltage	I <sub>S</sub> = 10 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	0.8	1.2	V
	L = 10 A; dL /dt = 100 A/vo; \/ = 0 \/;		20 E		no
reverse recovery time	$I_S$ = 10 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 25 V; $T_i$ = 25 °C	-	30.5	-	ns
	drain-source breakdown voltage  gate-source threshold voltage  drain leakage current  drain-source on-state resistance  racteristics FET1 and FET1 total gate charge gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time  diode FET1 and FET2 source-drain voltage	teristics FET1 and FET2		teristics FET1 and FET2           drain-source breakdown voltage $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ 80         -           gate-source threshold voltage $I_D = 1 \ mA; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C; \ Fig. 9; \ Fig. 10         2.4         3           I_D = 1 \ mA; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C; \ Fig. 9; \ Fig. 10         1         -         -           drain leakage current voltage         V_{DS} = 80 \ V; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C; \ Fig. 175 \ ^{\circ}C         -         -         0.03           drain-source on-state resistance         V_{GS} = 20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C; \ V_{GS} = 20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C; \ V_{GS} = 10 \ V; \ I_D = 10 \ A; \ T_j = 25 \ ^{\circ}C; \ Fig. 13; \ Fig. 14         -         -           racteristics FET1 and FET2         total gate charge gate-drain charge         I_D = 10 \ A; \ V_{DS} = 64 \ V; \ V_{GS} = 10 \ V; \ T_j = 175 \ ^{\circ}C; \ Fig. 13; \ Fig. 14         -         7.4           gate-drain charge         I_D = 10 \ A; \ V_{DS} = 64 \ V; \ V_{GS} = 10 \ V; \ T_j = 25 \ ^{\circ}C; \ Fig. 13; \ Fig. 14         -         7.4           output capacitance         V_{DS} = 25 \ V; \ V_{GS} = 0 \ V; \ F_j = 25 \ ^{\circ}C; \ Fig. 15         -         11.3           reverse transfer capacitance         V_{DS} = 60 \ V; \ R_i = 5 \ \Omega; \ V_{GS} = 10 \ V; \ R_j = 25 \ ^{\circ}C; \ Fig. 15         -         194           rise time  $	

#### Dual N-channel 80 V, 15 mΩ standard level MOSFET

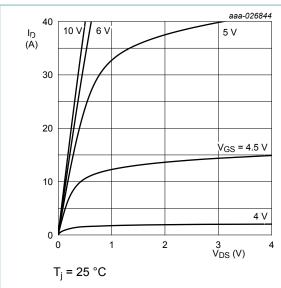


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values, FET1 and FET2

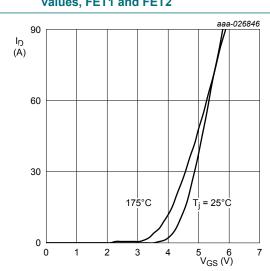


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values, FET1 and FET2

 $V_{DS}$  = 12 V

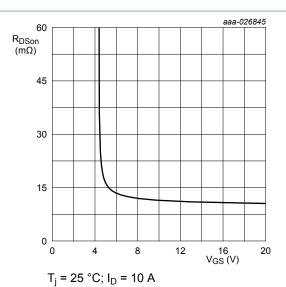


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values, FET1 and FET2

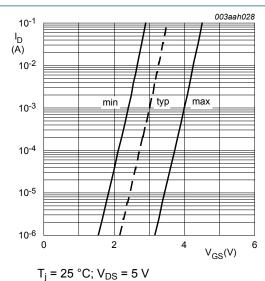


Fig. 9. Sub-threshold drain current as a function of gate-source voltage, FET1 and FET2

#### Dual N-channel 80 V, 15 mΩ standard level MOSFET

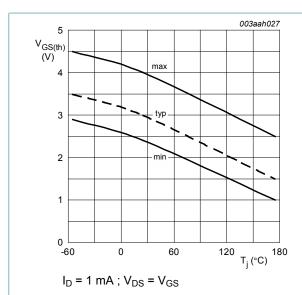


Fig. 10. Gate-source threshold voltage as a function of junction temperature, FET1 and FET2

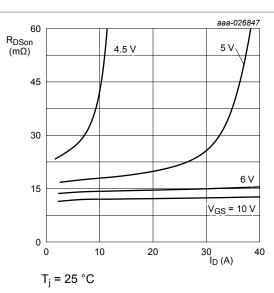


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values, FET1 and FET2

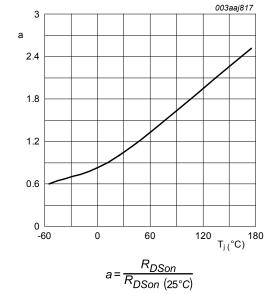


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature, FET1 and FET2

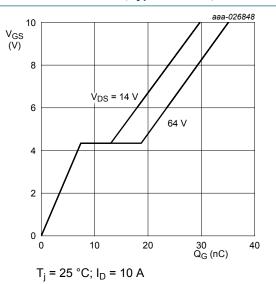


Fig. 13. Gate-source voltage as a function of gate charge; typical values, FET1 and FET2

#### Dual N-channel 80 V, 15 mΩ standard level MOSFET

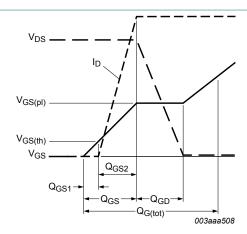
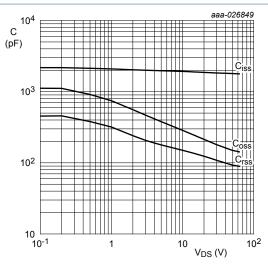
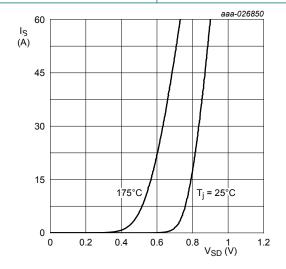


Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V$ ; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values, FET1 and FET2



 $V_{GS} = 0 V$ 

Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values, FET1 and FET2

#### Dual N-channel 80 V, 15 mΩ standard level MOSFET

# 11. Package outline

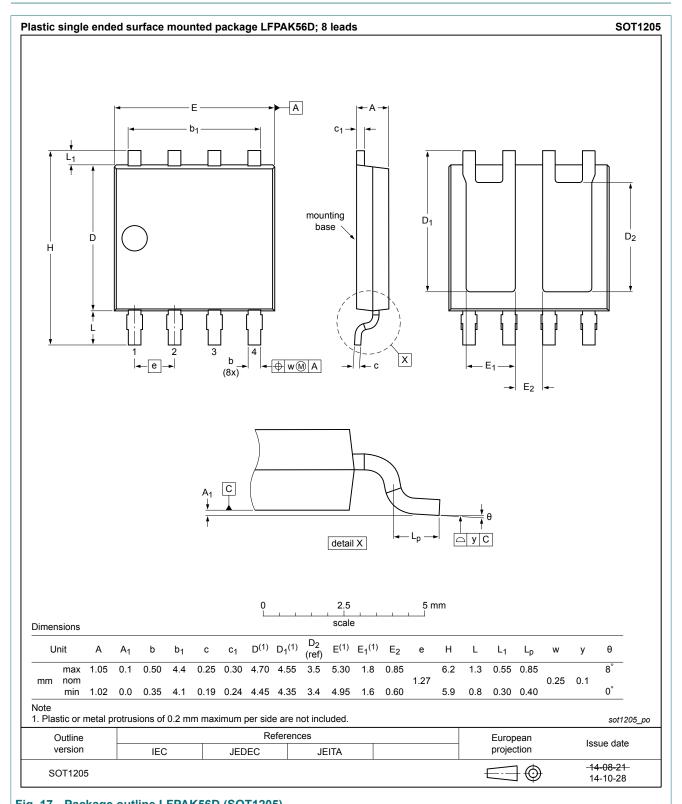


Fig. 17. Package outline LFPAK56D (SOT1205)

#### Dual N-channel 80 V, 15 mΩ standard level MOSFET

# 12. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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## Dual N-channel 80 V, 15 m $\Omega$ standard level MOSFET

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